



2CBG01,2CBG03,2CBG05

GLASS PASSIVATED SILICON FAST RECOVERY DIODE

Features:

1. Silicon diffusion mesa.
2. Glass Passivated package.
3. Small volume, light weight.
4. Small high-temperature leakage.
5. Good thermal stability.
6. High reliability.
7. Implementation of standards: GJB33A-97, QZJ840611A, QZJ840611



TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications			Test Condition
			2CBG01	2CBG03	2CBG05	
Use for	Ultra-high-frequency rectifier,switch circuit.					
Store temperature	T	°C	-55~+150			
Quality Class	JP, JT, JCT, GS, G, G+					
Peak Repetitive Reverse Voltage	V _{RRM}	V	2000~8000			
Average Forward Current	I _{F(AV)}	A	0.1	0.3	0.5	
Average Forward Voltage	V _F	V	B~E:8, F~H:10			I=I _{F(AV)}
Non-repeat Forward Surge Current	I _{FSM}	A	2	6	8	Single-phase industrial frequency sine half wave 10ms
Peak Reverse Current	I _{RM1}	uA	10			V _R =V _{RRM} , Ta=25°C
Peak Reverse Current	I _{RM2}	uA	200			V _R =V _{RRM} , Ta=125°C
Junction Temperature	T _{jm}	°C	125			
Reverse Recovery Time	t _{rr}	uS	0.8			V _R =10V,I _F =50mA,R _L =75ohms

SPECIFICATIONS:

B	C	D	E	F	G	H
2000V	3000V	4000V	5000V	6000V	7000V	8000V

Outline and Dimensions: